

2SK868, 2SK868A

Silicon N-channel Power F-MOS FET

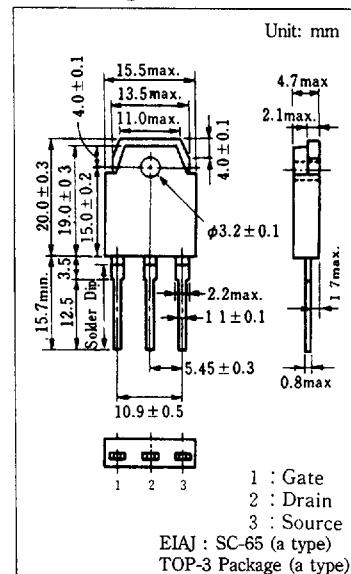
■ Features

- Low ON resistance $R_{DS(on)}$: $R_{DS(on)} = 0.2\Omega$ (typ.)
- High switching rate : $t_f = 150\text{ns}$ (typ.)
- No secondary breakdown
- High breakdown voltage, large power

■ Application

- No contact relay
- Solenoid drive
- Motor drive
- Control equipment
- Switching power source

■ Package Dimensions



■ Absolute Maximum Ratings ($T_c=25^\circ\text{C}$)

Item	Symbol	Value	Unit
Drain-source voltage	V_{DSS}	400	V
2SK868A	2SK868A	450	
Gate-source voltage	V_{GSS}	±20	V
Drain current	DC	I_D	A
Peak-to-peak value		I_{DP}	
Power dissipation	$T_c=25^\circ\text{C}$	P_D	W
Ta=25°C		130	
Channel temperature	T_{ch}	150	°C
Storage temperature	T_{stg}	-55~+150	°C

■ Electrical Characteristics ($T_c=25^\circ\text{C}$)

Item	Symbol	Condition	min.	typ.	max.	Unit
Drain current	I_{DSS}	$V_{DS}=320\text{V}, V_{GS}=0$			0.1	mA
Gate-source current	I_{GSS}	$V_{GS}=\pm 20\text{V}, V_{DS}=0$			±1	μA
Drain-source voltage	V_{DSS}	$I_D = 1\text{ mA}, V_{GS}=0$	400			V
2SK868A	2SK868A		450			
Gate threshold voltage	V_{th}	$V_{DS}=25\text{V}, I_D=1\text{mA}$	1		5	V
Drain-source ON resistance	$R_{DS(on)}$	$V_{GS}=10\text{V}, I_D=10\text{A}$		0.2	0.35	Ω
Drain-source ON voltage	$V_{DS(on)}$	$V_{GS}=10\text{V}, I_{DS}=20\text{A}$			8.0	V
Forward transfer admittance	Y _f	$V_{DS}=25\text{V}, I_D=10\text{A}$	7.2	12.0		S
Input capacitance	C_{iss}			3000		pF
Output capacitance	C_{oss}	$V_{DS}=20\text{V}, V_{GS}=0, f=1\text{MHz}$		430		pF
Reverse transfer capacitance	C_{rss}			175		pF
Turn-on time	t_{on}	$V_{GS}=10\text{V}, I_D=10\text{A}$ $V_{DD}=150\text{V}, R_L=15\text{Ω}$		150		ns
Fall time	t_f			150		ns
Delay time	$t_d(\text{off})$			520		ns

